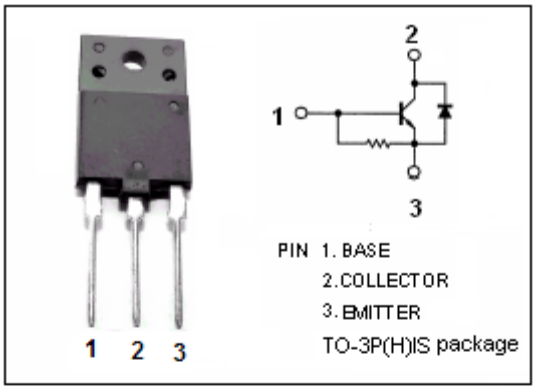
isc Silicon NPN Power Transistor 2SD2524

DESCRIPTION

- High Breakdown Voltage-
  : V_{CBO}= 1700V (Min)
- High Switching Speed
- Low Saturation Voltage
- Built-in Damper Diode

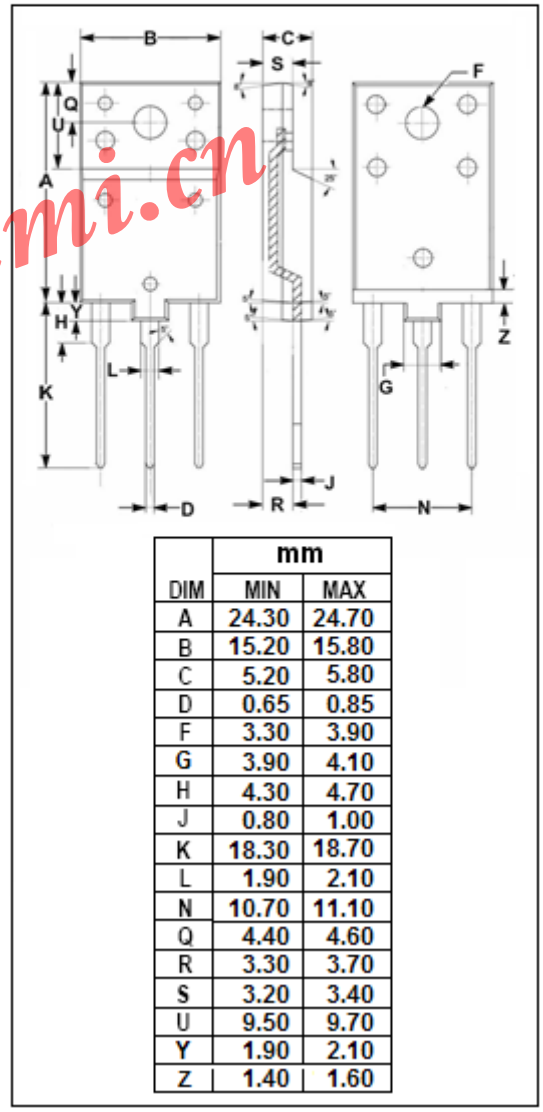


APPLICATIONS

- Designed for horizontal deflection output applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	1700	V
V_{CES}	Collector-Emitter Voltage	1700	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current- Continuous	8	A
I_{CM}	Collector Current-Peak	20	A
I_{BM}	Base Current-Peak	5	A
P_C	Collector Power Dissipation @ T_C=25℃	100	W
	Collector Power Dissipation @ T_a=25℃	3	
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



DIM	mm MIN	MAX
A	24.30	24.70
B	15.20	15.80
C	5.20	5.80
D	0.65	0.85
F	3.30	3.90
G	3.90	4.10
H	4.30	4.70
J	0.80	1.00
K	18.30	18.70
L	1.90	2.10
N	10.70	11.10
Q	4.40	4.60
R	3.30	3.70
S	3.20	3.40
U	9.50	9.70
Y	1.90	2.10
Z	1.40	1.60

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= 500mA ; I_C= 0	5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 6A; I_B= 2A			3.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 6A; I_B= 2A			1.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 1000V; I_E= 0			50	μA
		V_{CB}= 1700V; I_E= 0			1.0	mA
h_{FE}	DC Current Gain	I_C= 6A; V_{CE}= 5V	4		10	
V_{ECF}	C-E Diode Forward Voltage	I_F= 8A			2.0	V
f_T	Current-Gain—Bandwidth Product	I_C= 0.1A; V_{CE}= 10V		3		MHz

Resistive Load

t_s	Storage Time	I_C= 6A, $I_{B(end)}$= 2A, L_{leak}= 5μH			12	μs
t_f	Fall Time				0.8	μs